

an ohmic emitter contact connected to the layer of dielectric material and the emitter, the emitter contact having a top surface and a width that is greater than the width of the emitter; and

an ohmic base contact connected to the layer of dielectric material, the base contact having a top surface, being electrically connected to the base, and having a width that is less than the width of the emitter contact.

26. The device of claim 25 wherein the top surface of the emitter contact and the top surface of the base contact lie substantially in a same plane.

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27. The device of claim 26 and further comprising a base extender formed on the base, the base extender being formed from a second semiconductor material that is different from the first semiconductor material, the ohmic base contact being formed from a third semiconductor material different from the second semiconductor material.

28. An electrostatic discharge device formed in a semiconductor material, the device comprising:

- a collector of a first conductivity type formed in the semiconductor material;
- a base of a second conductivity type connected to the collector;
- an emitter of the first conductivity type connected to the base;
- a layer of dielectric material formed over the base;
- an emitter contact connected to the layer of dielectric material and the emitter; the emitter contact having a top surface;

- a base connector connected to the layer of dielectric material and the base, the base connector having a top surface; and

- a heat sink contact connected to the layer of dielectric material and the base, the heat sink contact being spaced apart and electrically isolated from the base connector, having a top surface, and contacting the top surface of the base.

29. The device of claim 28 wherein the base connector includes:
a base extender connected to an isolation region and the base region; and
a vertical base contact connected to the base extender and the layer of
dielectric material.

30. The device of claim 28 wherein the top surface of the emitter contact,
the top surface of the base connector, and the top surface of the heat sink contact
lie substantially in a same plane.

31. The device of claim 28 wherein:
the layer of dielectric material has a thermal conductivity; and
the heat sink contact has a thermal conductivity that is substantially greater
than the thermal conductivity of the layer of dielectric material.

32. The device of claim 28 wherein the heat sink contact has a single
electrical connection, the single electrical connection being to the base.--
